

**Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing**

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**Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons**

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**Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature**

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